

### General Description

These N-channel MOSFET are produced using advanced MagnaChip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

These devices are suitable device for SMPS, high Speed switching and general purpose applications.

### Features

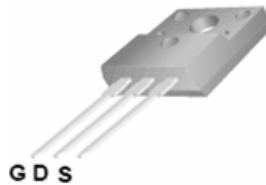
- $V_{DS} = 600V$
- $I_D = 6.0A$  @  $V_{GS} = 10V$
- $R_{DS(ON)} \leq 1.4\Omega$  @  $V_{GS} = 10V$

### Applications

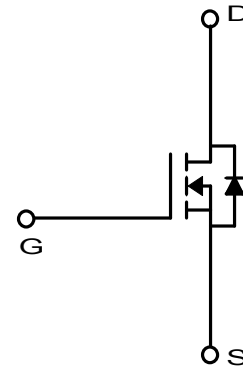
- Power Supply
- PFC
- High Current, High Speed Switching



TO-220  
MDP Series



TO-220F  
MDF Series



### Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics	Symbol	MDP6N60	MDF6N60	Unit	
Drain-Source Voltage	$V_{DSS}$	600		V	
Gate-Source Voltage	$V_{GSS}$	±30		V	
Continuous Drain Current	$I_D$	$T_C=25^\circ C$	6.0	6.0*	A
		$T_C=100^\circ C$	3.8	3.8*	A
Pulsed Drain Current <sup>(1)</sup>	$I_{DM}$	24	24*	A	
Power Dissipation	$P_D$	$T_C=25^\circ C$	131	37.9	W
		Derate above 25 °C	1.05	0.3	W/°C
Repetitive Avalanche Energy <sup>(1)</sup>	$E_{AR}$	13.1		mJ	
Peak Diode Recovery $dv/dt$ <sup>(3)</sup>	$dv/dt$	4.5		V/ns	
Single Pulse Avalanche Energy <sup>(4)</sup>	$E_{AS}$	220		mJ	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~150		°C	

\*  $I_D$  limited by maximum junction temperature

### Thermal Characteristics

Characteristics	Symbol	MDP6N60	MDF6N60	Unit
Thermal Resistance, Junction-to-Ambient <sup>(1)</sup>	$R_{\theta JA}$	62.5	62.5	°C/W
Thermal Resistance, Junction-to-Case <sup>(1)</sup>	$R_{\theta JC}$	0.95	3.3	

## Ordering Information

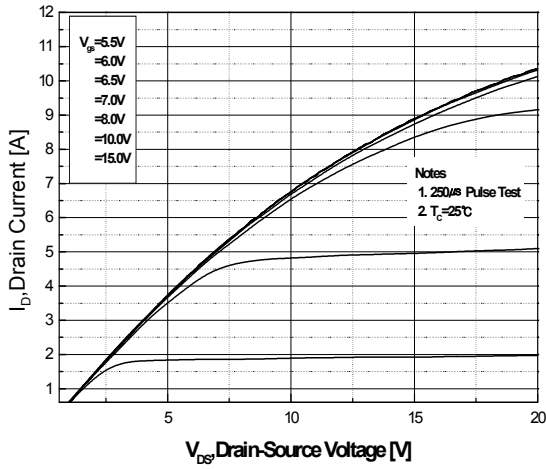
Part Number	Temp. Range	Package	Packing	RoHS Status
MDP6N60TH	-55~150°C	TO-220	Tube	Halogen Free
MDF6N60TH	-55~150°C	TO-220F	Tube	Halogen Free

## Electrical Characteristics (Ta =25°C)

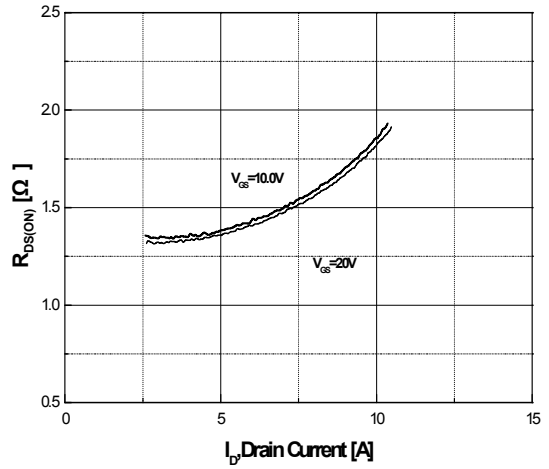
Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	600	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	-	5.0	
Drain Cut-Off Current	$I_{DSS}$	$V_{DS} = 600V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate Leakage Current	$I_{GSS}$	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3.0A$		1.2	1.4	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 30V, I_D = 3.0A$	-	5	-	S
<b>Dynamic Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 480V, I_D = 6.0A, V_{GS} = 10V^{(3)}$	-	15.4	-	nC
Gate-Source Charge	$Q_{gs}$		-	4.4	-	
Gate-Drain Charge	$Q_{gd}$		-	5.9	-	
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	-	660	860	pF
Reverse Transfer Capacitance	$C_{rss}$		-	3.2	5	
Output Capacitance	$C_{oss}$		-	78	100	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 300V, I_D = 6A, R_G = 25\Omega^{(3)}$	-	14		ns
Rise Time	$t_r$		-	23.2		
Turn-Off Delay Time	$t_{d(off)}$		-	32.2		
Fall Time	$t_f$		-	21.2		
<b>Drain-Source Body Diode Characteristics</b>						
Maximum Continuous Drain to Source Diode Forward Current	$I_S$		-	6.0	-	A
Source-Drain Diode Forward Voltage	$V_{SD}$	$I_S = 6.0A, V_{GS} = 0V$	-		1.4	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 6.0A, di/dt = 100A/\mu s^{(3)}$	-	275		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	2.1		$\mu C$

Note :

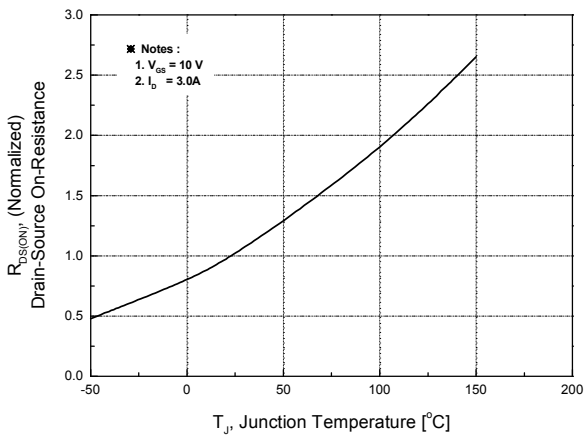
- Pulse width is based on  $R_{\theta JC}$  &  $R_{\theta JA}$  and the maximum allowed junction temperature of 150°C.
- Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ , pulse width limited by junction temperature  $T_{J(MAX)}=150^\circ C$ .
- $I_{SD} \leq 6.0A$ ,  $di/dt \leq 200A/\mu s$ ,  $V_{DD}=50V$ ,  $R_G = 25\Omega$ , Starting  $T_J=25^\circ C$
- $L=8.7mH$ ,  $I_{AS}=6.0A$ ,  $V_{DD}=50V$ ,  $R_G = 25\Omega$ , Starting  $T_J=25^\circ C$ ,



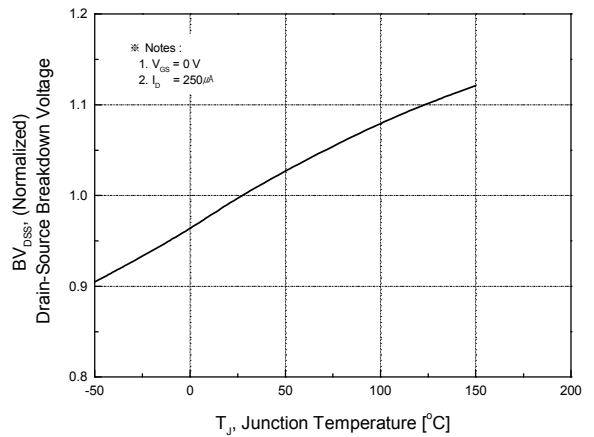
**Fig.1 On-Region Characteristics**



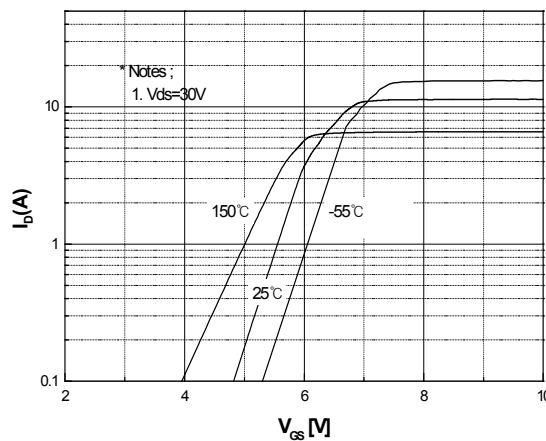
**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**



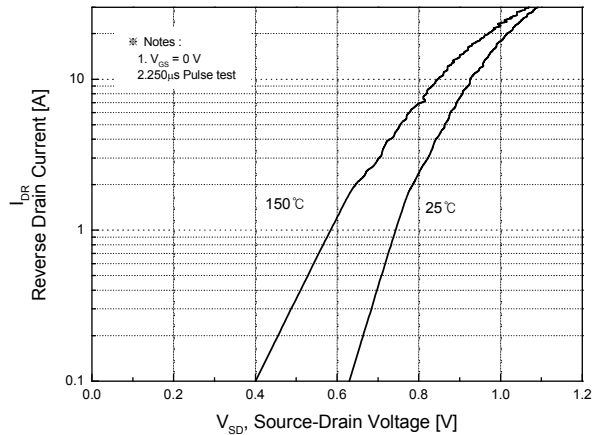
**Fig.3 On-Resistance Variation with Temperature**



**Fig.4 Breakdown Voltage Variation vs. Temperature**



**Fig.5 Transfer Characteristics**



**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**

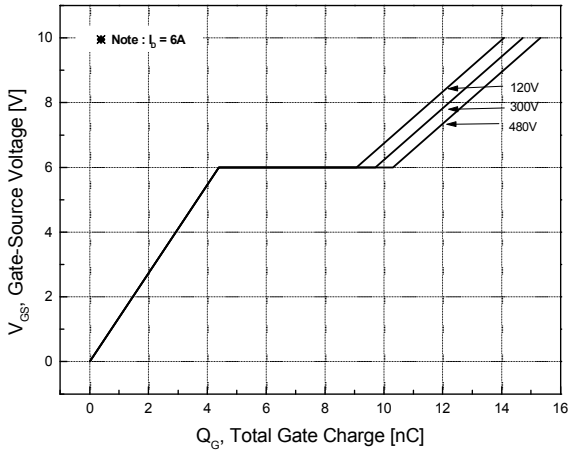


Fig.7 Gate Charge Characteristics

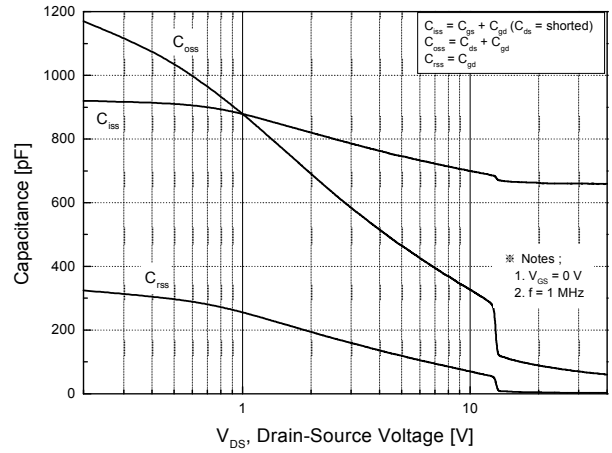


Fig.8 Capacitance Characteristics

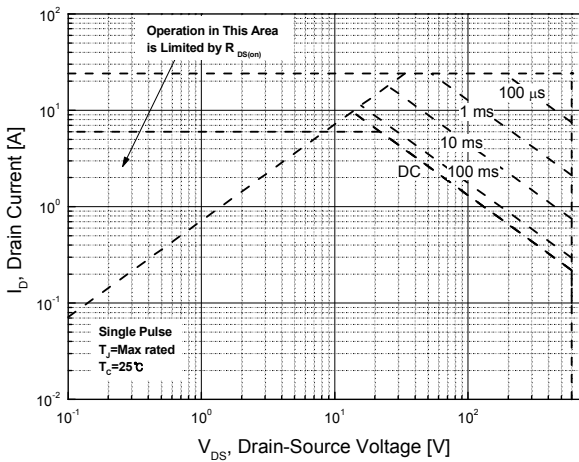


Fig.9 Maximum Safe Operating Area MDP6N60(TO-220)

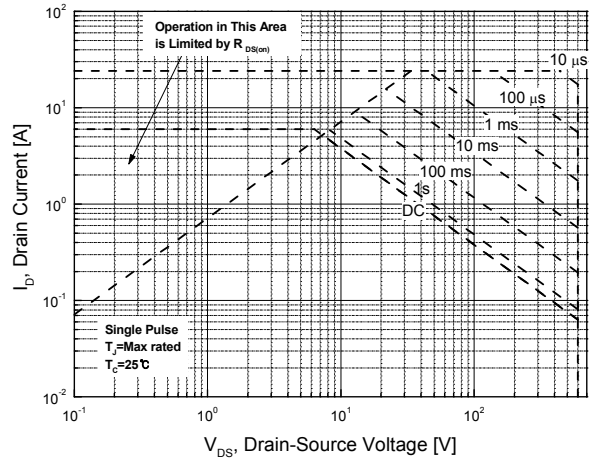


Fig.10 Maximum Safe Operating Area MDF6N60(TO-220F)

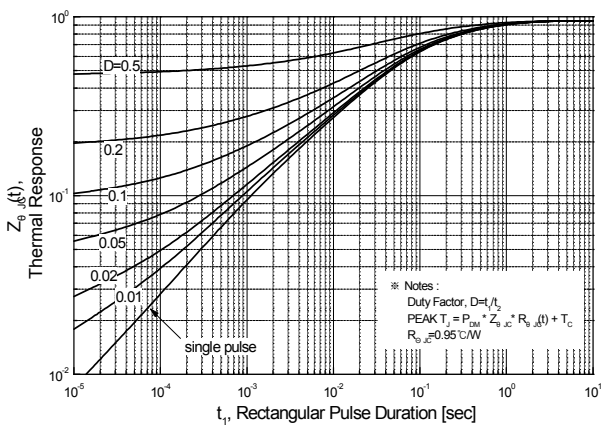


Fig.11 Transient Thermal Response Curve MDP6N60(TO-220)

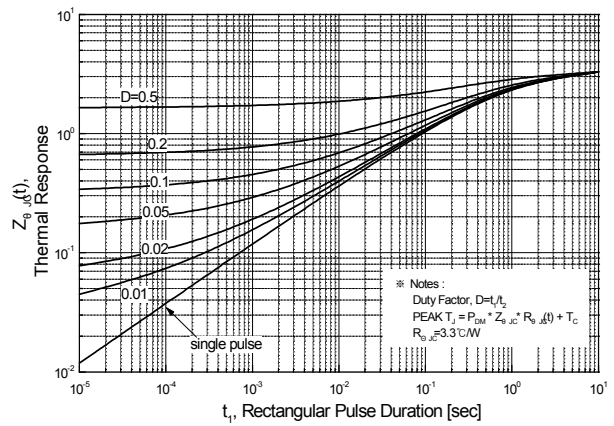
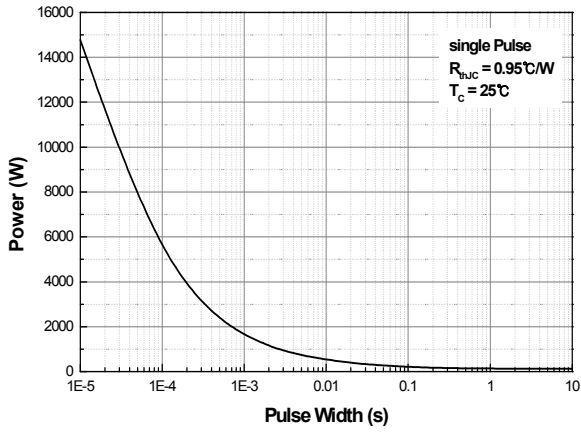
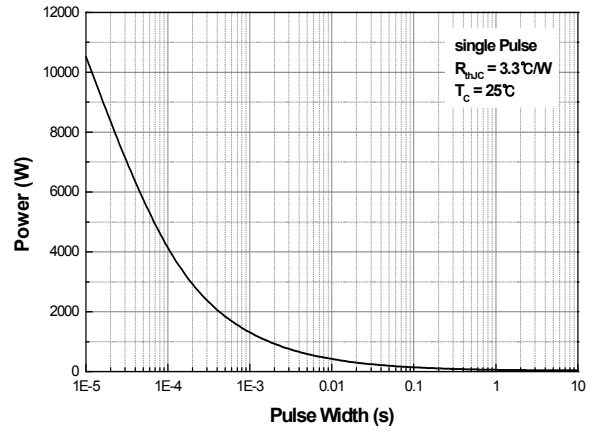


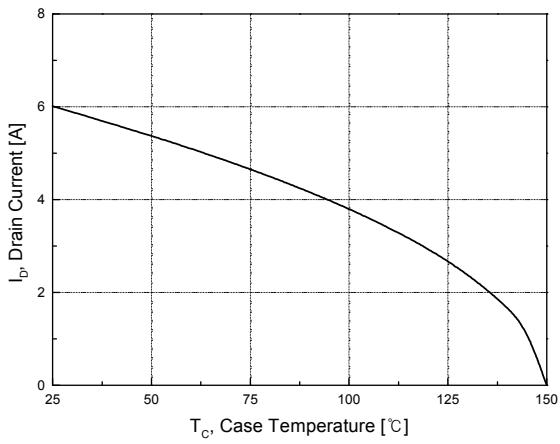
Fig.12 Transient Thermal Response Curve MDF6N60(TO-220F)



**Fig.13 Single Pulse Maximum Power Dissipation MDP6N60(TO-220)**



**Fig.14 Single Pulse Maximum Power Dissipation MDF6N60(TO-220F)**

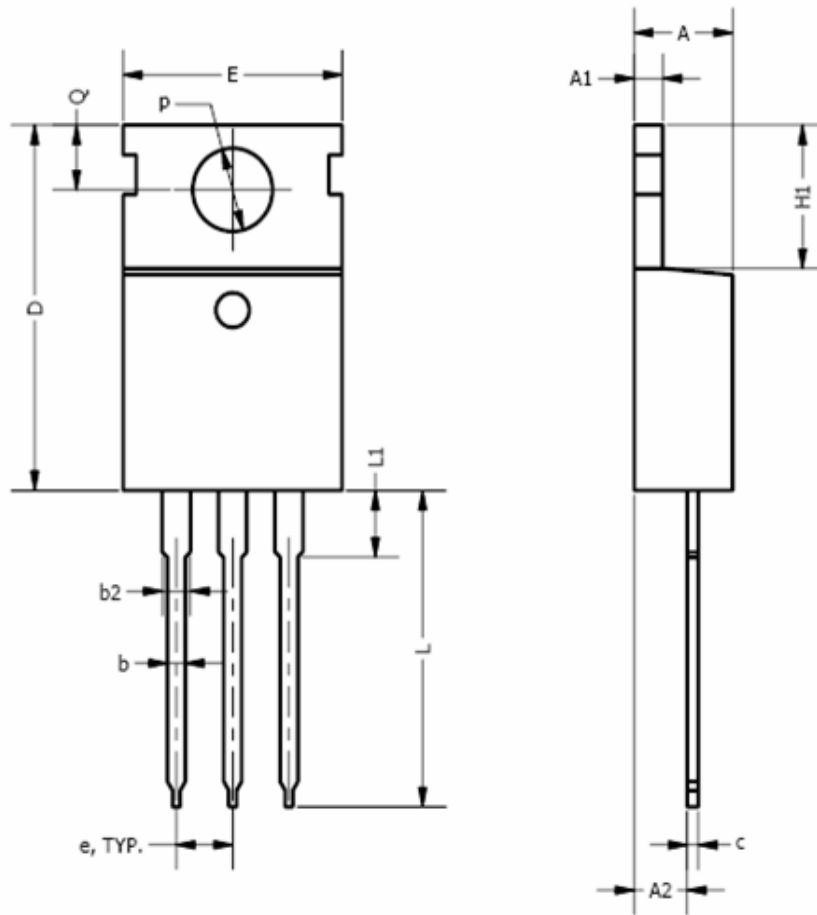


**Fig.15 Maximum Drain Current vs. Case Temperature**

**Physical Dimensions**

**3 Leads, TO-220**

Dimensions are in millimeters unless otherwise specified

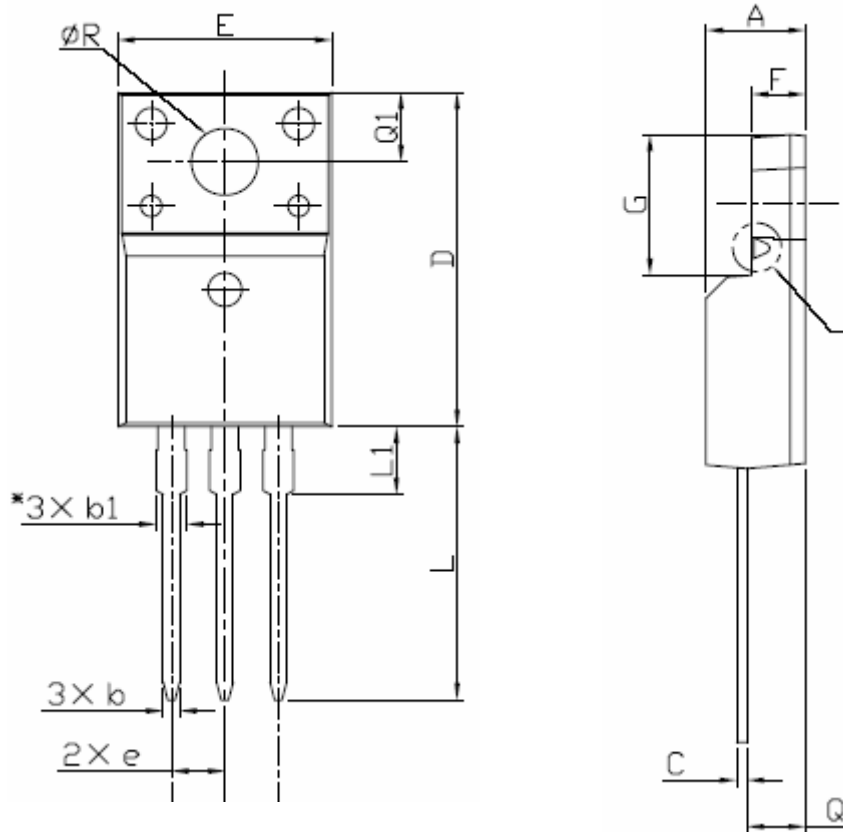


Symbol	Min	Nom	Max
A	3.56		4.83
A1	0.50		1.40
A2	2.03		2.92
b	0.38	0.69	1.02
b2	1.14	1.45	1.78
c	0.36		0.61
D	14.22		16.51
e	2.54 TYP		
E	9.65		10.67
H1	5.84		6.86
L	12.70		14.73
L1			6.35
$\phi P$	3.53		4.09
Q	2.54		3.43

## Physical Dimensions

## 3 Leads, TO-220F

Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	4.50		4.93
b	0.63		0.91
b1	1.15		1.47
C	0.33		0.63
D	15.47		16.13
E	9.60		10.71
e		2.54	
F	2.34		2.84
G	6.48		6.90
L	12.24		13.72
L1	2.79		3.67
Q	2.52		2.96
Q1	3.10		3.50
ØR	3.00		3.55

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